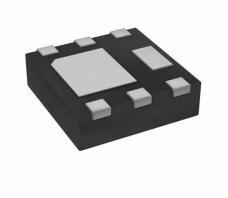


DMN3042LFDF-13 Datasheet

www.digi-electronics.com



https://www.DiGi-Electronics.com

DiGi Electronics Part Number DMN3042LFDF-13-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number DMN3042LFDF-13

Description MOSFET N-CH 30V 7A 6UDFN

Detailed Description N-Channel 30 V 7A (Ta) 2.1W (Ta) Surface Mount U-

DFN2020-6 (Type F)



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:					
DMN3042LFDF-13	Diodes Incorporated					
Series:	Product Status:					
	Active					
FET Type:	Technology:					
N-Channel	MOSFET (Metal Oxide)					
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:					
30 V	7A (Ta)					
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ Id, Vgs:					
2.5V, 10V	28mOhm @ 4A, 10V					
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:					
1.4V @ 250µA	13.3 nC @ 10 V					
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:					
±12V	570 pF @ 50 V					
FET Feature:	Power Dissipation (Max):					
	2.1W (Ta)					
Operating Temperature:	Mounting Type:					
-55°C ~ 150°C (TJ)	Surface Mount					
Supplier Device Package:	Package / Case:					
U-DFN2020-6 (Type F)	6-UDFN Exposed Pad					
Base Product Number:						
DMN3042						

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	





30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on) Max	I _D Max T _A = +25°C
	28mΩ @ V _{GS} = 10V	7.0A
30V	32mΩ @ V _{GS} = 4.5V	6.5A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

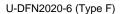
- General Purpose Interfacing Switch
- Power Management Functions

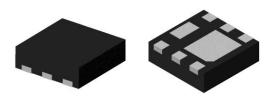
Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

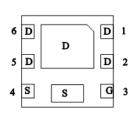
Mechanical Data

- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 Per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208
- Weight: 0.007 grams (Approximate)

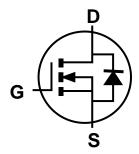




Top View Bottom View



Pin Out Bottom View



Internal Schematic

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN3042LFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMN3042LFDF-13	U-DFN2020-6 (Type F)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1



S7 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Kev

Date Code Ney												
Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н		J	K	L	M	Ν	0	Р	R
	_											
		l.	1	1		I	l.		_			
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



S7 = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016	 2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6	 0	1	2	3	4	5	6	7	8	9

Week	1-26	27-52	53
Code	A-Z	a-z	z

Internal Code	Sun	Mon	Tue	Wed	Thu	Fri	Sat
Code	Т	U	V	W	X	Y	Z



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Drain-Source Voltage		VDSS	30	V	
Gate-Source Voltage		V_{GSS}	±12	V	
Continuous Drain Current (Note 6) Vgs = 10V	T _A = +25°C T _A = +70°C	lo	7.0 5.6	А	
Maximum Continuous Body Diode Forward Curre	nt (Note 6)		Is	1.5	Α
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1	%)		I _{DM}	35	A
Avalanche Current (L = 0.1mH) (Note 7)		las	13	Α	
Avalanche Energy (L = 0.1mH) (Note 7)			Eas	9	mJ

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)	$T_A = +25^{\circ}C$	PD	0.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	Б	177	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	124	C/VV	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	P_{D}	2.1	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	D	61	°C/W	
Thermal Resistance, Junction to Ambient (Note o)	t<10s	$R_{\theta JA}$	43	C/VV	
Thermal Resistance, Junction to Case	Steady State	$R_{\theta JC}$	9.3	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					•	
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0V, I_{D} = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	0.6		1.4	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
			17	28		$V_{GS} = 10V, I_{D} = 4.0A$
Static Drain-Source On-Resistance	Dagger	_	20	32	mΩ	$V_{GS} = 4.5V, I_D = 4.0A$
Static Drain-Source On-Resistance	RDS(ON)	_	24	42	11112	Vgs = 3.0V, ID = 4.0A
		_	28	50		$V_{GS} = 2.5V, I_{D} = 4.0A$
Diode Forward Voltage	V_{SD}	_	0.7	1.2	V	V _{GS} = 0V, I _S = 1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	l	570	_		45)/)/ 0)/
Output Capacitance	Coss		63	_	pF	V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	53	_		1 = 1.0IVII IZ
Gate Resistance	Rg	_	3.2	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = 10V)	Qg	_	13.3	_		
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	6.1	_	nC	V 45V L COA
Gate-Source Charge	Qgs	_	1.0		nc nc	$V_{DS} = 15V, I_{D} = 6.9A$
Gate-Drain Charge	Q_{gd}	_	1.6	_		
Turn-On Delay Time	t _{D(ON)}	_	1.5			
Turn-On Rise Time	t _R	_	3.3	_	no	$V_{GS} = 10V, V_{DD} = 15V, R_g = 3\Omega,$
Turn-Off Delay Time	t _{D(OFF)}	_	13.9	_	ns	I _D = 6.9A
Turn-Off Fall Time	tF	_	4.9	_		
Body Diode Reverse Recovery Time	trr		7.8	_	ns	Is = 5A, dI/dt = 100A/µs
Body Diode Reverse Recovery Charge	Qrr		1.9		nC	Is = 5A, dI/dt = 100A/µs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

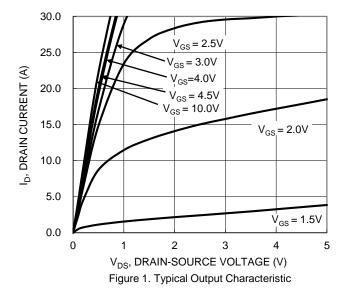
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.





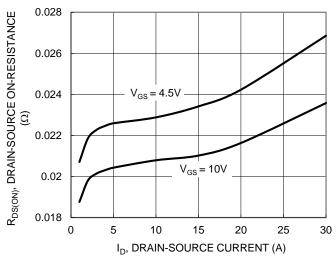


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

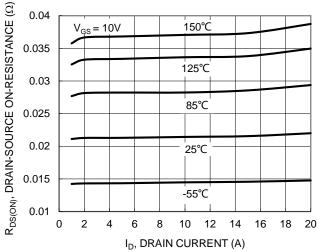


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

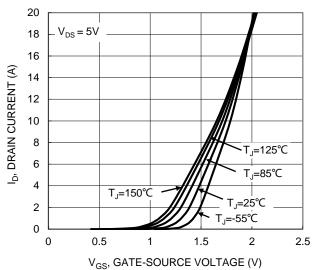


Figure 2. Typical Transfer Characteristic

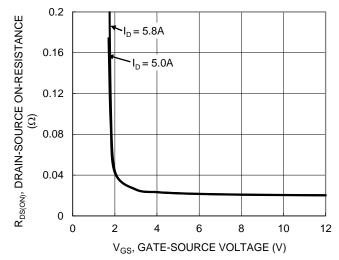


Figure 4. Typical Transfer Characteristic

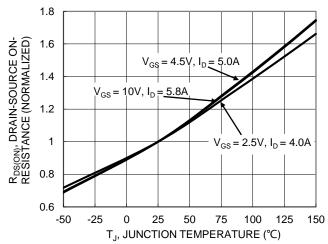


Figure 6. On-Resistance Variation with Temperature



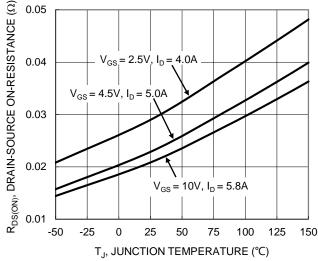


Figure 7. On-Resistance Variation with Temperature

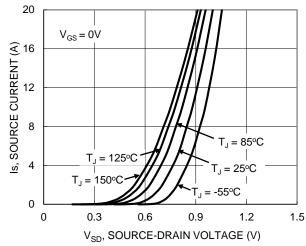


Figure 9. Diode Forward Voltage vs. Current

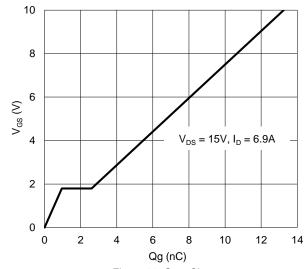


Figure 11. Gate Charge

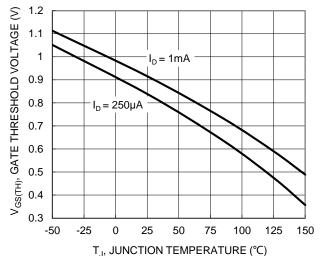


Figure 8. Gate Threshold Variation vs. Junction Temperature

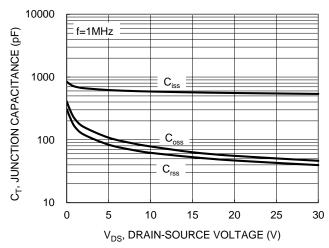
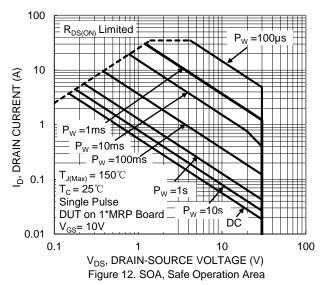


Figure 10. Typical Junction Capacitance





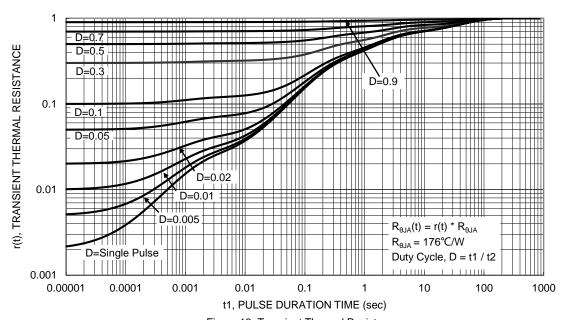


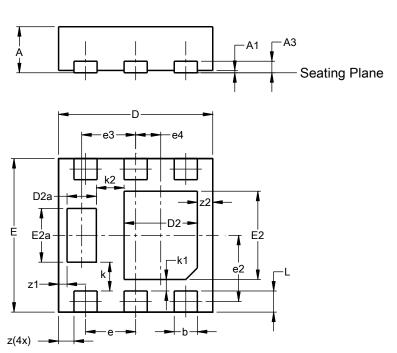
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

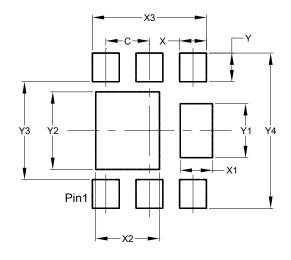


	U-DFN2020-6 (Type F)								
Dim	Min Max Typ								
Α	0.57	0.60							
A1	0.00	0.03							
A3	-	0.05	0.15						
b	0.25	0.35	0.30						
D	1.95	2.05	2.00						
D2	0.85	1.05	0.95						
D2a	0.33	0.43	0.38						
Е	1.95	2.05	2.00						
E2	1.05	1.25	1.15						
E2a	0.65	0.75	0.70						
е		0.65 BS	С						
e2	().863 BS	SC SC						
е3		0.70 BS	С						
e4).325 BS							
k		0.37 BS							
k1		0.15 BS							
k2		0.36 BS							
L		0.325							
Z	0.20 BSC								
z1).110 BS							
z2		0.20 BS	С						
All C	Dimens	ions in	mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value
	(in mm)
С	0.650
X	0.400
X1	0.480
X2	0.950
Х3	1.700
Y	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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